## NSN 5961-01-167-0060

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-167-0060 **Inclosure Material:** Metal and ceramic **Overall Length:** Between 12.45 millimeters and 15.24 millimeters **Overall Diameter:** Between 36.07 millimeters and 43.18 millimeters Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-200ab **Mounting Method:** Compression **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 600.0 repetitive peak off-state voltage and 3.0 gate trigger voltage, instantaneous **Current Rating Per Characteristic:** 260.00 amperes forward current, total rms pascal and 17.00 milliamperes forward current, total rms **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Terminal Type And Quantity:** 2 case and 1 quick disconnect, male and 1 solder stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: